RENESAS HD74LVC4245A

Octal Bus Transceiver and 3.3 V to 5 V shifters with 3-state Outputs

REJ03D0378-0100 (Previous ADE-205-683 (Z)) Rev.1.00 Aug. 20, 2004

Description

The HD74LVC4245A has eight bus transceivers with three state outputs in a 24 pin package. When (DIR) is high, data flows from the A inputs to the B outputs, and when (DIR) is low, data flows from the B inputs to the A outputs. A and B bus are separated by making enable input $\overline{(OE)}$ high level. And this product has two terminals (V_{CCA}, V_{CCB}), V_{CCA} (5V) is connected with control input and A bus side, V_{CCB} (3.3V) connected with B bus side. V_{CCA} and V_{CCB} are isolated. This allows for translation from a 3.3 V to a 5 V environment, and vice versa. Low voltage and high-speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- This product function as level shift transceiver that change V_{CCA} input level to V_{CCB} output level, V_{CCB} input level to V_{CCA} output level by providing different supply voltage to V_{CCA} and V_{CCB} .
- This product is able to the power management: Turn on and off the supply on V_{CCB} side with providing the supply of V_{CCA} . (Enable input (\overline{OE}): High level)
- $V_{CCA} = 4.5 \text{ V}$ to 5.5 V, $V_{CCB} = 2.7 \text{ V}$ to 3.6 V
- All control input V_I (max) = 5.5 V (@V_{CCA} = 0 V to 5.5 V)
- All A bus side input outputs V_{I/O} (max) = 5.5 V (@V_{CCA} = 0 V or output off state)
- All B bus side input outputs V_{I/O} (max) = 3.6 V (@V_{CCB} = 0 V or output off state)
- High output current
 A bus side : ±24 mA (@V_{CCA} = 4.5 V to 5.5 V)

 B bus side : ±12 mA (@V_{CCB} = 2.7 V)
 ±24 mA (@V_{CCB} = 3.0 V to 3.6 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LVC4245ATEL	TSSOP-24 pin	TTP–24DBV	Т	EL (1,000 pcs/reel)



Function Table

Inputs

ŌĒ	DIR	Operation	
L	L	B data to A bus	
L	Н	A data to B bus	
Н	Х	Z	

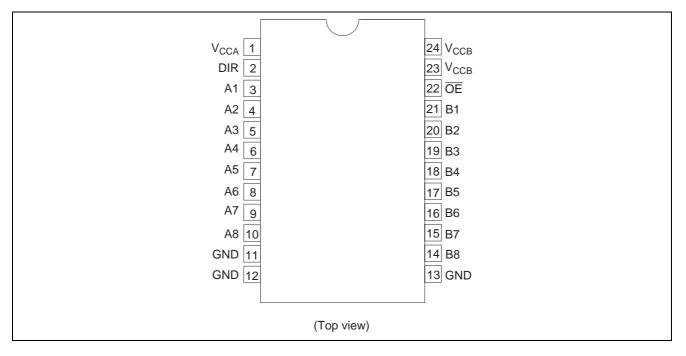
H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement





Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CCA}	–0.5 to 6.0	V	
Input voltage ^{*1}	VI	–0.5 to 6.0	V	DIR, OE
Input / output voltage	V _{I/O}	-0.5 to V _{CCA} +0.5	V	A port output "H" or "L"
		-0.5 to 6.0		A port output "Z" or V _{CCA} : OFF
Input diode current	I _{IK}	-50	mA	V ₁ < 0
Output diode current	I _{ОК}	-50	mA	V ₀ < 0
		50		$V_{\rm O} > V_{\rm CCA} + 0.5$
Output current	lo	±50	mA	
V _{CCA} , GND current	I _{CCA} or I _{GN}	_D 100	mA	
Maximum power dissipation at Ta = 25°C (in still air) ^{*2}	P _T	862	mW	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.

2. The maximum package power dissipation was calculated using a junction temperature of 150°C.

				(2) For V_{CCB}
Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CCB}	-0.5 to 4.6	V	
Input / output voltage ^{*1}	V _{I/O}	–0.5 to V _{CCB} +0.5	V	B port output "H" or "L"
		-0.5 to 4.6		B port output "Z" or V_{CCB} : OFF
Input diode current	I _{IK}	-50	mA	V ₁ < 0
Output diode current	loк	-50	mA	V ₀ < 0
		50		V _O > V _{CCB} +0.5
Output current	lo	±50	mA	
V _{CCB} ,GND current	I _{CCB} or I _{GND}	100	mA	
Maximum power dissipation	Pτ	862	mW	TSSOP
at Ta = 25°C (in still air) ^{*2}				
Storage temperature	Tstg	-65 to 150	°C	

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(1) For V_{CCA}

Recommended Operating Conditions

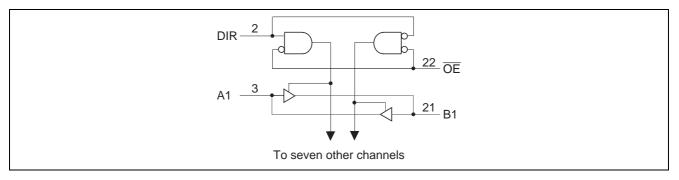
Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CCA}	4.5 to 5.5	V	
Input / output voltage	VI	0 to 5.5	V	DIR, OE
	V _{I/O}	0 to V _{CCA}		A port output "H" or "L"
		0 to 5.5		A port output "Z" or V _{CCA} : OFF
Output current	I _{OH}	-24	mA	
	I _{OL}	24		
Input transition rise or fall time	$\Delta t / \Delta v$	10	ns / V	
Operating temperature	Та	-40 to 85	°C	

Note: Unused or floating inputs must be held high or low.

				(2) For V_{CCB}
Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CCB}	2.7 to 3.6	V	
Input / output voltage	V _{I/O}	0 to V _{CCB}	V	B port output "H" or "L"
		0 to 3.6		B port output "Z" or V_{CCB} : OFF
Output current	I _{OH}	–12	mA	V _{CCB} = 2.7 V
		-24		V _{CCB} = 3.0 to 3.6 V
	I _{OL}	12		V _{CCB} = 2.7 V
		24		V _{CCB} = 3.0 to 3.6 V
Input transition rise or fall time	Δt / Δv	10	ns / V	
Operating temperature	Та	-40 to 85	°C	

Note: Unused or floating inputs must be held high or low.

Block Diagram



(1) For V_{CCA}

Electrical Characteristics

							$(Ta = -40 \text{ to } 85^{\circ}C)$
Item	Symbol	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit	Test Conditions
Input voltage	VIH	4.5 to 5.5	2.7 to 3.6	2	_	V	
	VIL	4.5 to 5.5	2.7 to 3.6	_	0.8		
Output voltage	V _{OHA}	4.5 to 5.5	2.7 to 3.6	V _{CCA} -0.2	_	V	I _{OH} = −100 μA
		4.5	2.7 to 3.6	3.7	_		I _{OH} = -24 mA
		5.5	2.7 to 3.6	4.7	—		
	V _{OHB}	4.5 to 5.5	2.7 to 3.6	V _{CCB} 0.2	—	V	I _{OH} = −100 μA
		4.5 to 5.5	2.7	2.2	_		I _{OH} = -12 mА
		4.5 to 5.5	3.0	2.4	_		
		4.5 to 5.5	3.0	2	_		I _{OH} = -24 mA
	V _{OLA}	4.5 to 5.5	2.7 to 3.6		0.2	V	I _{OL} = 100 μA
		4.5	2.7 to 3.6	_	0.55		I _{OL} = 24 mA
		5.5	2.7 to 3.6		0.55		
	V _{OLB}	4.5 to 5.5	2.7 to 3.6		0.2	V	I _{OL} = 100 μA
		4.5 to 5.5	2.7		0.4		I _{OL} = 12 mA
		4.5 to 5.5	3.0		0.55		I _{OL} = 24 mA
Input current	I _{IN}	5.5	2.7 to 3.6		±1	μA	Control input
Off state	I _{OZA}	5.5	2.7 to 3.6		±5	μA	A port, $V_0 = V_{CCA}$ or GND
output current	I _{OZB}	4.5 to 5.5	3.6		±5		B port, $V_0 = V_{CCB}$ or GND
Output leak current	I _{OFF}	0	0	_	20	μA	A port, $V_{I/O} = 5.5 V$
							B port, $V_{I/O}$ = 3.6 V
Quiescent	I _{CCA}	5.5	2.7 to 3.6	_	80	μA	B to A,
supply current							control input =V _{CCA} or GND
							$Bn = V_{CCB}$ or GND ,
							I_O (A port) = 0
	I _{CCB}	4.5 to 5.5	3.6	_	50	μA	A to B,
							control input =V _{CCA} or GND
							An = V_{CCA} or GND,
							I_O (B port) = 0
Increase in I _{CC}	ΔI_{CCA}	5.5	2.7 to 3.6	_	1.5	mA	A port or Control input,
per input *1							One input at 3.4 V,
							Other input at V _{CCA} at GND
	ΔI_{CCB}	4.5 to 5.5	2.7 to 3.6	_	0.5	mA	B port,
							One input at V _{CCB} –0.6V,
							Other input at V _{CCB} at GND

Notes: For condition shown as Min or Max, use the appropriate values under recommended operating conditions.
 1. This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.



Capacitance

								$(Ta = 25^{\circ}C)$
Item	Symbol	V _{CCA} (V)	V _{CCB} (V)	Min	Тур	Max	Unit	Test Conditions
Control Input capacitance	CIN	5	3.3	_	5	_	рF	$V_I = V_{CCA}$ or GND
Input/output capacitance	C _{I/O}	5	3.3	—	11	—	pF	A port, $V_1 = V_{CCA}$ or GND, B port, $V_1 = V_{CCB}$ or GND

Switching Characteristics

					(Ta = -	$-40 \text{ to } 85^{\circ}\text{C}$), $V_{\text{CCA}} = 5$	0.0 ± 0.5 V, V _{CCB}	= 2.7 V to 3.6 V
Item	Symbol	Min	Тур	Max	Unit	Test conditions	From(Input)	To(Output)
Propagation delay	t _{PLH}	1	_	6.7	ns	C _L = 50 pF	А	В
time	t _{PHL}	1	—	6.3		$R_L = 500 \ \Omega$		
	t _{PLH}	1	—	5			В	А
	t _{PHL}	1	—	6.1				
Output enable time	t _{ZH}	1	—	8.1	ns	C _L = 50 pF	ŌĒ	А
	t _{ZL}	1	—	9		$R_L = 500 \ \Omega$		
	t _{ZH}	1	—	9.8			ŌĒ	В
	t _{ZL}	1	_	8.8				
Output disable time	t _{HZ}	1	_	5.8	ns	C _L = 50 pF	OE	А
	t _{LZ}	1	_	7		$R_L = 500 \ \Omega$		
	t _{HZ}	1	_	7.8			OE	В
	t _{LZ}	1	_	7.7				

Operating Characteristics

Item	Symbol	V _{CCA} (V)	V _{CCB} (V)	Min	Тур	Мах	Unit	Test Conditions
Power dissipation capacitance	CPD	5.0	3.0	_	39.5	_	рF	$f = 10 \text{ MHz}, C_{L} = 0$

Power-up considerations

Level-translation devices offer an opportunity for successful mixed-voltage signal design.

A proper power-up sequence always should be followed to avoid excessive supply current, bus contention, oscillations, or other anomalies caused by improperly biased device pins.

Take these precautions to guard against such power-up problems.

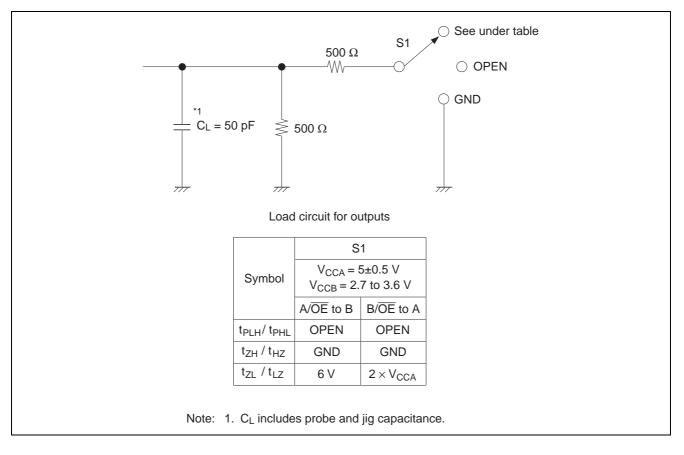
- 1. Connect ground before any supply voltage is applied.
- 2. Next, power up the control side of the device. (Power up of V_{CCA} is first. Next power up is V_{CCB} .)
- 3. Tie \overline{OE} to V_{CCA} with a pullup resistor so that it ramps with V_{CCA}.
- 4. Depending on the direction of the data path, DIR can be high or low.

If DIR high is needed (A data to B bus), ramp it with V_{CCA}. Overwise, keep DIR low.



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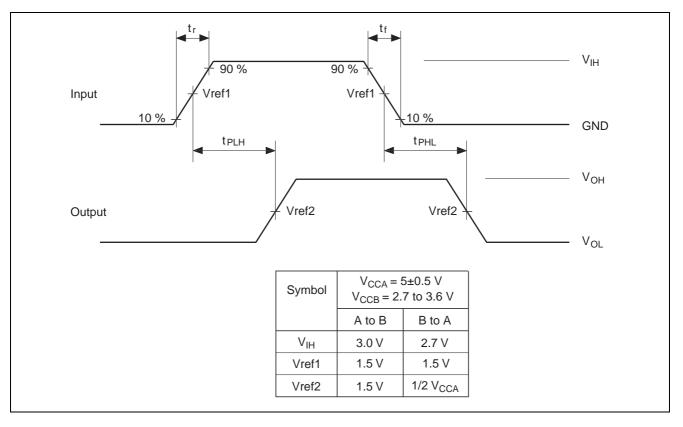
Test Circuit





HD74LVC4245A

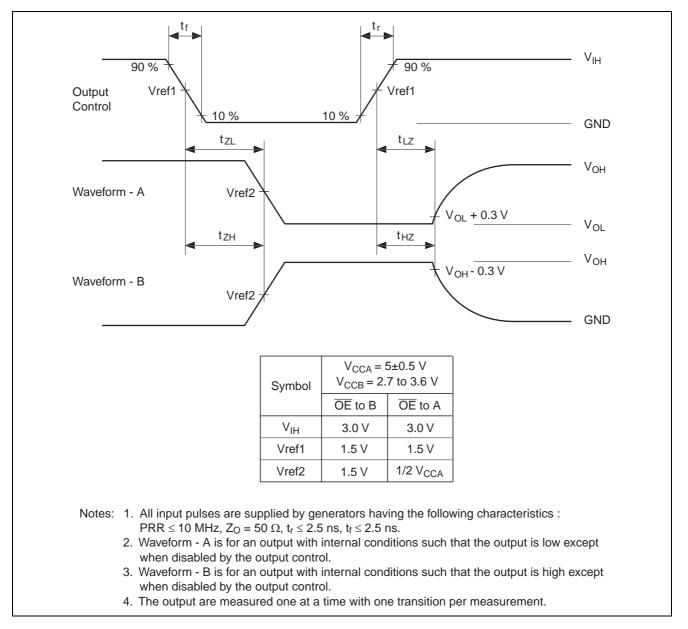
Waveforms - 1





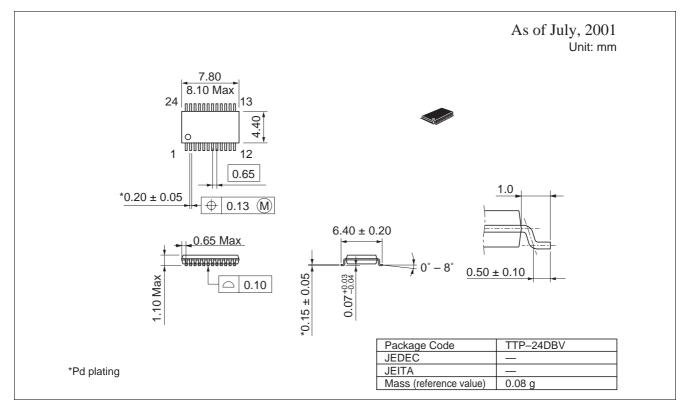
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Waveforms - 2





Package Dimensions



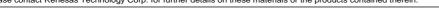


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